

L Number	Hits	Search Text	DB	Time stamp
1	0	"GaN.sub.0.97Psub.0.03"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 09:55
2	0	"Ga N.sub.0.97 P.sub.0.03"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 09:56
3	0	"Ga N.sub."\$6 near2 "P.sub."\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 09:58
4	7	"Ga N.sub."	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 09:58
5	0	"GaN.sub."	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 09:59
6	94	"GaN.sub"\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 10:00
7	12	"GaN.sub"\$6 and (BP or boron adj phosphide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 10:01
9	0	"GaP.sub"\$6 near20 (BP or boron adj phosphide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 10:01
8	4	"GaN.sub"\$6 near20 (BP or boron adj phosphide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 10:04
10	2	"GaN.sub"\$6 near20 buffer and (BP or boron adj phosphide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 10:05
11	1024	mixed adj crystal.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 10:06
12	103	mixed adj crystal.ti. and (single-crystal or single adj crystal or single-crystalline or single adj crystalline or monocrystal or monocrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 11:27
13	2	lattice adj match\$3 near20 (boron adj phosphide or BP) near20 (gallium adj nitride or GaN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 11:28

14	2	(lattice-match\$3 lattice adj match\$3) near20 (boron adj phosphide or BP) near20 (gallium adj nitride or GaN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 11:36
15	86	(gan or gallium adj nitride) near20 (boron adj phosphide or bp)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 11:37
16	13	(gan or gallium adj nitride) near20 (boron adj phosphide or bp) near20 buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 12:35
17	173	(gan or gallium adj nitride) near20 lattice adj constant	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 13:39
18	11	(gan or gallium adj nitride) near20 buffer adj layer near20 (boron adj phosphide or bp)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 13:40
19	5	(single-crystal or single adj crystal or monocrystalline) near20 (gan or gallium adj nitride) near20 buffer adj layer near20 (boron adj phosphide or bp)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 13:47
20	556	(vapor adj phase adj growth or CVD) near3 (single-crystal or single adj crystal or monocrystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 13:56
21	192	(vapor adj phase adj growth or CVD) near3 (single-crystal or single adj crystal or monocrystal).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 14:37
22	1	increase near12 lattice adj parameter near12 (phosphorous or phosphorus)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 15:52
23	2	("5042043").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 15:52
-	0	("(GaN or gallium adj nitride adj phosphide) and light-emitting.ti,ab. ").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/16 09:55
-	12	(GaN or gallium adj nitride adj phosphide) and light-emitting.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 07:10
-	4	(GaN or "GaN.sub.1-x.P.sub.x" or gallium adj nitride adj phosphide) and light-emitting.ti,ab. and boron adj phosphide near3 buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 16:53
-	4	(GaN or "GaN.sub.1-x.P.sub.x" or gallium adj nitride adj phosphide) and light-emitting.ti,ab. and (BP or boron adj phosphide) near6 buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 16:54

-	7	(GaNP or "GaN.sub.1-x.P.sub.x" or gallium adj nitride adj phosphide or GaN near6 P or GaN near6 phosphorus or gallium adj nitride near6 (phosphorus or P)) and light-emitting.ti.ab. and (BP or boron adj phosphide) near6 buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 16:58
-	4	(GaNP or "GaN.sub.1-x.P.sub.x" or gallium adj nitride adj phosphide or GaN near6 P or GaN near6 phosphorus or gallium adj nitride near6 (phosphorus or P)) and (257/8\$5.ccls. or 257/9\$5.ccls. or 257/100.ccls. or 257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and (BP or boron adj phosphide) near6 buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:07
-	4	(GaNP or GaPN or gallium adj phosphide adj nitride or "GaN.sub.x.P.sub.1-x" or "GaN.sub.1-x.P.sub.x" or gallium adj nitride adj phosphide or GaN near6 P or GaN near6 phosphorus or gallium adj nitride near6 (phosphorus or P)) and (257/8\$5.ccls. or 257/9\$5.ccls. or 257/100.ccls. or 257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and (BP or boron adj phosphide) near6 buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:09
-	4	(GaNP or GaPN or gallium adj phosphide adj nitride or "GaN.sub.x.P.sub.1-x" or "GaN.sub.1-x.P.sub.x" or gallium adj nitride adj phosphide or GaN near6 P or GaN near6 phosphorus or gallium adj nitride near6 (phosphorus or P) or GaN near6 (P or phosphorus)) and (257/8\$5.ccls. or 257/9\$5.ccls. or 257/100.ccls. or 257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and (BP or boron adj phosphide) near6 buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:10
-	4	(GaNP or GaPN or gallium adj phosphide adj nitride or "GaN.sub.x.P.sub.1-x" or "GaN.sub.1-x.P.sub.x" or gallium adj nitride adj phosphide or GaN near6 P or GaN near6 phosphorus or gallium adj nitride near6 (phosphorus or P) or (gallium adj nitride or GaN) near6 (P or phosphorus)) and (257/8\$5.ccls. or 257/9\$5.ccls. or 257/100.ccls. or 257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and (BP or boron adj phosphide) near6 buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:28
-	342	(GaNP or GaPN or gallium adj phosphide adj nitride or "GaN.sub.x.P.sub.1-x" or "GaN.sub.1-x.P.sub.x" or gallium adj nitride adj phosphide or GaN near6 P or GaN near6 phosphorus or gallium adj nitride near6 (phosphorus or P) or (gallium adj nitride or GaN) near6 (P or phosphorus)) and (257/8\$5.ccls. or 257/9\$5.ccls. or 257/100.ccls. or 257/101.ccls. or 257/102.ccls. or 257/103.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:29
-	275	(GaNP or GaPN or gallium adj phosphide adj nitride or "GaN.sub.x.P.sub.1-x" or "GaN.sub.1-x.P.sub.x" or gallium adj nitride adj phosphide or GaN near6 P or GaN near6 phosphorus or gallium adj nitride near6 (phosphorus or P) or (gallium adj nitride or GaN) near6 (P or phosphorus)) and (257/8\$5.ccls. or 257/9\$5.ccls. or 257/100.ccls. or 257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:30

-	4	(GaNP or GaPN or gallium adj phosphide adj nitride or "GaN.sub.x.P.sub.1-x" or "GaN.sub.1-x.P.sub.x" or gallium adj nitride adj phosphide or GaN near6 P or GaN near6 phosphorus or gallium adj nitride near6 (phosphorus or P) or (gallium adj nitride or GaN) near6 (P or phosphorus)) and (257/8\$5.ccls. or 257/9\$5.ccls. or 257/100.ccls. or 257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and buffer near12 (boron adj phosphide or bp)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:34
-	489	(257/79).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:35
-	435	(257/80).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:35
-	366	(257/81).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:35
-	814	(257/82).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:35
-	106	(257/83).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:35
-	380	(257/84).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:35
-	205	(257/85).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:35
-	229	(257/86).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:35
-	56	(257/87).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:35
-	488	(257/88).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:35
-	175	(257/89).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:35

-	83	(257/90).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:36
-	147	(257/91).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:36
-	49	(257/92).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:36
-	146	(257/93).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:36
-	685	(257/94).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:36
-	239	(257/95).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:36
-	445	(257/96).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:36
-	327	(257/97).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:36
-	1241	(257/98).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:36
-	1351	(257/99).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:36
-	318	(257/100).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:36
-	278	(257/101).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:36
-	308	(257/102).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:36
-	967	(257/103).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:37

-	0	("L13 or L14 or L15 or L16 or L17 or L18 or L19 or L20 or L21 or L22 or L23 or L24 or L25 or L26 or L27 or L28 or L29 or L30 or L31 or L32 or L33 or L34 or L35 or L36 or L37").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:38
-	6890	((257/79).CCLS.) or ((257/80).CCLS.) or ((257/81).CCLS.) or ((257/82).CCLS.) or ((257/83).CCLS.) or ((257/84).CCLS.) or ((257/85).CCLS.) or ((257/86).CCLS.) or ((257/87).CCLS.) or ((257/88).CCLS.) or ((257/89).CCLS.) or ((257/90).CCLS.) or ((257/91).CCLS.) or ((257/92).CCLS.) or ((257/93).CCLS.) or ((257/94).CCLS.) or ((257/95).CCLS.) or ((257/96).CCLS.) or ((257/97).CCLS.) or ((257/98).CCLS.) or ((257/99).CCLS.) or ((257/100).CCLS.) or ((257/101).CCLS.) or ((257/102).CCLS.) or ((257/103).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:40
-	0	((257/79).CCLS.) or ((257/80).CCLS.) or ((257/81).CCLS.) or ((257/82).CCLS.) or ((257/83).CCLS.) or ((257/84).CCLS.) or ((257/85).CCLS.) or ((257/86).CCLS.) or ((257/87).CCLS.) or ((257/88).CCLS.) or ((257/89).CCLS.) or ((257/90).CCLS.) or ((257/91).CCLS.) or ((257/92).CCLS.) or ((257/93).CCLS.) or ((257/94).CCLS.) or ((257/95).CCLS.) or ((257/96).CCLS.) or ((257/97).CCLS.) or ((257/98).CCLS.) or ((257/99).CCLS.) or ((257/100).CCLS.) or ((257/101).CCLS.) or ((257/102).CCLS.) or ((257/103).CCLS.) and ganp.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:41
-	13	((257/79).CCLS.) or ((257/80).CCLS.) or ((257/81).CCLS.) or ((257/82).CCLS.) or ((257/83).CCLS.) or ((257/84).CCLS.) or ((257/85).CCLS.) or ((257/86).CCLS.) or ((257/87).CCLS.) or ((257/88).CCLS.) or ((257/89).CCLS.) or ((257/90).CCLS.) or ((257/91).CCLS.) or ((257/92).CCLS.) or ((257/93).CCLS.) or ((257/94).CCLS.) or ((257/95).CCLS.) or ((257/96).CCLS.) or ((257/97).CCLS.) or ((257/98).CCLS.) or ((257/99).CCLS.) or ((257/100).CCLS.) or ((257/101).CCLS.) or ((257/102).CCLS.) or ((257/103).CCLS.) and (ganp or (gan or gallium adj nitride) near12 phosphorus)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:43
-	2	((257/79).CCLS.) or ((257/80).CCLS.) or ((257/81).CCLS.) or ((257/82).CCLS.) or ((257/83).CCLS.) or ((257/84).CCLS.) or ((257/85).CCLS.) or ((257/86).CCLS.) or ((257/87).CCLS.) or ((257/88).CCLS.) or ((257/89).CCLS.) or ((257/90).CCLS.) or ((257/91).CCLS.) or ((257/92).CCLS.) or ((257/93).CCLS.) or ((257/94).CCLS.) or ((257/95).CCLS.) or ((257/96).CCLS.) or ((257/97).CCLS.) or ((257/98).CCLS.) or ((257/99).CCLS.) or ((257/100).CCLS.) or ((257/101).CCLS.) or ((257/102).CCLS.) or ((257/103).CCLS.) and buffer near12 (bp or boron adj phosphide) and (ganp or (gan or gallium adj nitride) near12 phosphorus)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:44

-	13	((257/79).CCLS.) or ((257/80).CCLS.) or ((257/81).CCLS.) or ((257/82).CCLS.) or ((257/83).CCLS.) or ((257/84).CCLS.) or ((257/85).CCLS.) or ((257/86).CCLS.) or ((257/87).CCLS.) or ((257/88).CCLS.) or ((257/89).CCLS.) or ((257/90).CCLS.) or ((257/91).CCLS.) or ((257/92).CCLS.) or ((257/93).CCLS.) or ((257/94).CCLS.) or ((257/95).CCLS.) or ((257/96).CCLS.) or ((257/97).CCLS.) or ((257/98).CCLS.) or ((257/99).CCLS.) or ((257/100).CCLS.) or ((257/101).CCLS.) or ((257/102).CCLS.) or ((257/103).CCLS.)) and (ganp or (gan or gallium adj nitride) near12 phosphorus)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:47
-	4	((257/79).CCLS.) or ((257/80).CCLS.) or ((257/81).CCLS.) or ((257/82).CCLS.) or ((257/83).CCLS.) or ((257/84).CCLS.) or ((257/85).CCLS.) or ((257/86).CCLS.) or ((257/87).CCLS.) or ((257/88).CCLS.) or ((257/89).CCLS.) or ((257/90).CCLS.) or ((257/91).CCLS.) or ((257/92).CCLS.) or ((257/93).CCLS.) or ((257/94).CCLS.) or ((257/95).CCLS.) or ((257/96).CCLS.) or ((257/97).CCLS.) or ((257/98).CCLS.) or ((257/99).CCLS.) or ((257/100).CCLS.) or ((257/101).CCLS.) or ((257/102).CCLS.) or ((257/103).CCLS.)) and (gan or gallium adj nitride) and ((bp or boron adj phosphide) near12 buffer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:53
-	0	jp-410242514\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:54
-	2	jp-10242514\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:56
-	2	jp-10242567\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:59
-	2	jp-10242569\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:09
-	2	6316793.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:10
-	2	6064082.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:11
-	2	5929467.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:11
-	2	jp-10066769\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 20:04
-	0	jp-410066769\$-\$.did.	JPO	2002/05/30 20:05

-	1	jp-10066769\$-\$.did.	JPO	2002/05/30 20:06
-	1	jp-11036830\$-\$.did.	JPO	2002/05/30 20:06
-	0	jp-411036830\$-\$.did.	JPO	2002/05/30 20:06
-	0	terashima.in. and buffer	JPO	2002/05/30 20:13
-	1	light-emitting.ti,ab. and ((bp or boron adj phosphide) near10 buffer) and gallium adj nitride.ti,ab.	JPO	2002/05/30 20:14
-	1	light-emitting.ti,ab. and ((bp or boron adj phosphide) near10 buffer) and gallium adj nitride	JPO	2002/05/30 20:14
-	3	(led or light-emitting or light adj emitting).ti,ab. and ((bp or boron adj phosphide) near10 buffer) and gallium adj nitride	JPO	2002/05/30 20:15
-	4	(GaN or gallium adj nitride adj phosphide or AlGaN or aluminum adj gallium adj nitride adj phosphide or "GaN.sub.lix.P.sub.x") and light-emitting.ti,ab. and buffer near10 (bp or boron adj phosphide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 07:13
-	4	(GaN or gallium adj nitride adj phosphide or AlGaN or aluminum adj gallium adj nitride adj phosphide or "GaN.sub.1-x.P.sub.x") and light-emitting.ti,ab. and (bp or boron adj phosphide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 07:15
-	8	((GaN or gallium adj nitride or AlGaN or aluminum adj gallium adj nitride) near6 (P or phosphide)) and light-emitting.ti,ab. and (bp or boron adj phosphide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 07:19
-	7	((GaN or gallium adj nitride or AlGaN or aluminum adj gallium adj nitride) near6 (P or phosphide)) and light-emitting.ti,ab. and ((bp or boron adj phosphide) near10 buffer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 07:58
-	4	((GaN or gallium adj nitride or AlGaN or aluminum adj gallium adj nitride) near6 (P or phosphide)) and light-emitting.ti,ab. and ((bp or boron adj phosphide) near10 buffer) and (mono-crystal or single adj crystal) near6 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 08:01
-	8	light-emitting.ti,ab. and ((bp or boron adj phosphide) near10 buffer) and (mono-crystal or single adj crystal) near6 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 08:01
-	325	light-emitting.ti,ab. and ((mono-crystal or single adj crystal) near6 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 08:15
-	184	light-emitting.ti,ab. and ((mono-crystal or single adj crystal) adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 08:16
-	14	light-emitting.ti,ab. and ((mono-crystal or single adj crystal) adj substrate) and GaN.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 08:17



-	351	buffer adj layer near3 amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 08:43
-	4	(bp or boron adj phosphorus) near6 buffer adj layer near3 amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 08:44
-	38	amorphous adj buffer adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 10:42
-	3	amorphous adj buffer adj layer and (single adj crystal or single-crystal) adj buffer adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 11:23
-	64	single adj (heterojunction or hetero-junction) and (double adj heterojunction or hetero-junction) and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 11:26
-	58	(single adj (heterojunction or hetero-junction)) and (double adj (heterojunction or hetero-junction)) and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 12:36
-	2	("6150672").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 11:47
-	4	(single adj (heterojunction or hetero-junction)).ti,ab. and (double adj (heterojunction or hetero-junction)) and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 13:07
-	2	("6150672").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 13:41
-	1	(lattice near6 (match\$3 or mismatch\$3)) near12 (boron adj phosphide or BP or BPN or "BP.sub.1-x.N.sub.x") near12 (GaN or gallium adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:47
-	1	(lattice near6 (match\$3 or mismatch\$3)) near12 (boron adj phosphide or BP or BPN or "BP.sub.1-x.N.sub.x") near12 (GaN or gallium adj nitride or AlGaN or aluminum adj gallium adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 13:44
-	29	((boron adj phosphide or bp) near12 buffer) near12 (N or nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 14:11
-	1	(lattice near6 (match\$3 or mismatch\$3)) near12 (boron adj phosphide or BP or BPN or "BP.sub.1-x.N.sub.x") near12 (GaN or gallium adj nitride or gallium adj nitride adj phosphide or GaNP)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:59
-	1	(lattice near6 (match\$3 or mismatch\$3) or lattice-match\$3 or lattice-mismatch\$3) near12 (boron adj phosphide or BP or BPN or "BP.sub.1-x.N.sub.x") near12 (GaN or gallium adj nitride or gallium adj nitride adj phosphide or GaNP)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 16:16

-	1	(lattice near6 (match\$3 or mismatch\$3) or lattice-match\$3 or lattice-mismatch\$3) near12 (boron adj phosphide or BP or BPN or "BP.sub.1-x.N.sub.x" or BNP or "BN.sub.1-x.P.sub.x") near12 (GaN or gallium adj nitride or gallium adj nitride adj phosphide or GaNP)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 16:33
-	66	(boron adj phosphide or BP or BPN or "BP.sub.1-x.N.sub.x" or BNP or "BN.sub.1-x.P.sub.x") near12 (GaN or gallium adj nitride or gallium adj nitride adj phosphide or GaNP)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 17:58
-	0	"10-066769"	JPO	2002/05/31 17:59
-	1	jp-10066769\$-\$.did.	JPO	2002/05/31 18:00
-	1	jp-10180921\$-\$.did.	JPO	2002/05/31 18:01
-	0	jp-410180921\$-\$.did.	JPO	2002/05/31 18:01
-	0	terashima.in. and semiconductor	JPO	2002/05/31 18:12
-	2	terashima.in. and "1998"	JPO	2002/05/31 18:14
-	1	jp-10066769\$-\$.did.	JPO	2002/05/31 18:15
-	1	jp-10180921\$-\$.did.	JPO	2002/05/31 18:16
-	1	jp-10193125\$-\$.did.	JPO	2002/05/31 18:17
-	1	jp-10232279\$-\$.did.	JPO	2002/05/31 18:17
-	1	jp-11036830\$-\$.did.	JPO	2002/05/31 18:18
-	2301	udagawa.in.	JPO	2002/05/31 18:18
-	35	udagawa.in. and light-emitting	JPO	2002/05/31 18:18
-	3	udagawa.in. and light-emitting and (BP or boron adj phosphide)	JPO	2002/05/31 18:22
-	0	terashima.in. and light-emitting and (BP or boron adj phosphide)	JPO	2002/05/31 18:23
-	0	nishimura.in. and light-emitting and (BP or boron adj phosphide)	JPO	2002/05/31 18:23
-	0	tsuzaki.in. and light-emitting and (BP or boron adj phosphide)	JPO	2002/05/31 18:23
-	11550	boron adj phosphide or bp	DERWENT	2002/05/31 18:25
-	245	(boron adj phosphide or bp) and buffer	DERWENT	2002/05/31 18:25
-	15	(boron adj phosphide or bp) and buffer adj layer	DERWENT	2002/05/31 18:25
-	62	udagawa.in. and light-emitting	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 10:52
-	1076	udagawa.in. and light-emitting and buffer near6 BP or BNP or BPN or "BN.sub.1-x.P.sub.x" or "BP.sub.x.N.sub.1-x" or "BN.sub.x.P.sub.1-x" or "BP.sub.1-x.N.sub.x" or ((BP or boron adj phosphide) near3 nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 10:56
-	8	udagawa.in. and light-emitting and (buffer near6 (BP or BNP or BPN or "BN.sub.1-x.P.sub.x" or "BP.sub.x.N.sub.1-x" or "BN.sub.x.P.sub.1-x" or "BP.sub.1-x.N.sub.x" or ((BP or boron adj phosphide) near3 nitrogen)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 11:22

-	2	terashima.in. and light-emitting and (buffer near6 (BP or BNP or BPN or "BN.sub.1-x.P.sub.x" or "BP.sub.x.N.sub.1-x" or "BN.sub.x.P.sub.1-x" or "BP.sub.1-x.N.sub.x" or ((BP or boron adj phosphide) near3 nitrogen)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 13:29
-	9	light-emitting.ti,ab. and (buffer near6 (BP or BN or BNP or BPN or "BN.sub.1-x.P.sub.x" or "BP.sub.x.N.sub.1-x" or "BN.sub.x.P.sub.1-x" or "BP.sub.1-x.N.sub.x"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 13:35
-	0	(lattice adj match\$3 or mismatch\$3) and (((BN or boron adj nitride) near3 buffer) near10 (phosphorus or P)) and (GaN or gallium adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 13:39
-	0	(lattice adj match\$3 or mismatch\$3) and (((BN or boron adj nitride) near6 buffer) near10 (phosphorus or P))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 13:39
-	0	(lattice adj (match\$3 or mismatch\$3)) and (((BN or boron adj nitride) near6 buffer) near10 (phosphorus or P))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 13:40
-	0	(lattice adj (match\$3 or mismatch\$3)) and (((BN or BNP or BPN or boron adj nitride) near6 buffer) near10 (phosphorus or P))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 13:41
-	0	(lattice near6 (match\$3 or mismatch\$3)) and (((BN or BNP or BPN or boron adj nitride) near6 buffer) near10 (phosphorus or P))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 13:42
-	672	(boron adj nitride or BN or boron adj phosphide or BP or BNP) near6 buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 13:43
-	99	(boron adj nitride or BN or boron adj phosphide or BP or BNP) near6 buffer and (GaN or gallium nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 14:48
-	54	(boron adj nitride or BN or BNP) near6 buffer and (GaN or gallium nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 14:50
-	16	(boron adj nitride or BN or BNP) near6 buffer and (GaN or gallium nitride) and (lattice-mismatch or lattice-match\$3 or (lattice near3 (match\$3 or mismatch\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 14:52
-	15	(boron adj nitride or BN or BNP) near6 buffer and (GaN or gallium nitride) near12 (lattice-mismatch or lattice-match\$3 or (lattice near3 (match\$3 or mismatch\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 15:39
-	0	gallium adj nitride adj phosphide and light-emitting.ti,ab. and phosphorus	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 15:40

-	7	(GaN <sub>P</sub> or "GaN.sub.1-x.P.sub.x" or gallium adj nitride adj phosphide) and light-emitting.ti,ab. and (phosphorus or P)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 15:42
-	0	(GaN <sub>P</sub> or "GaN.sub.1-x.P.sub.x" or gallium adj nitride adj phosphide) and light-emitting.ti,ab. and phosphorus	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 15:43
-	2	(GaN <sub>P</sub> or "GaN.sub.1-x.P.sub.x" or gallium adj nitride adj phosphide) and light-emitting.ti,ab. and phosphorus	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 17:21
-	2	lamp.ti,ab. and light-emitting.ti,ab. and semiconductor.ti,ab. and group adj "III-V"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 17:23
-	6	lamp.ti,ab. and light-emitting.ti,ab. and semiconductor.ti,ab. and GaN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 17:31
-	8	lamp.ti,ab. and light-emitting.ti,ab. and GaN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 17:31
-	3	lamp.ti,ab. and light-emitting.ti,ab. and GaN and mount\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 18:57
-	4	((("5042043") or ("6372356") or ("5612551") or ("5326424")).PN.	USPAT	2002/06/01 19:01
-	7496	((257/79) or (257/85) or (257/86) or (257/94) or (257/102) or (257/103) or (372/43)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 19:23
-	3	((257/79) or (257/85) or (257/86) or (257/94) or (257/102) or (257/103) or (372/43)).CCLS.) and (gallium adj nitride or gallium adj phosphide or GaN or GaP or "GaN.sub.1-x.P.sub.x" or "GaN.sub.x.P.sub.1-x") and buffer near4 (BN or BP or BNP or BPN or "BN.sub.x.P.1-x" or "BN.sub.1-x.P.sub.x" or boron adj nitride or boron adj phosphide) and (lattice near12 (match\$3 or mismatch\$3) or lattice-match\$3 or lattice-mismatch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 19:28
-	2	("5042043").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 14:02
-	21	(US-6392257-\$ or US-5326424-\$ or US-6069021-\$ or US-6316793-\$ or US-6150672-\$ or US-5612551-\$ or US-5929467-\$ or US-5042043-\$ or US-6194744-\$ or US-6064082-\$).did. or (US-20020038892-\$ or US-20020030246-\$ or US-20020000563-\$).did. or (JP-11045892-\$ or JP-10242567-\$ or JP-10242514-\$ or JP-10242569-\$).did. or (JP-2000332294-\$ or JP-2000004046-\$ or JP-2000188260-\$ or EP-395392-\$).did.	USPAT; US-PGPUB; JPO; DERWENT	2002/11/10 14:08

-	13	((US-6392257-\$ or US-5326424-\$ or US-6069021-\$ or US-6316793-\$ or US-6150672-\$ or US-5612551-\$ or US-5929467-\$ or US-5042043-\$ or US-6194744-\$ or US-6064082-\$).did. or (US-20020038892-\$ or US-20020030246-\$ or US-20020000563-\$).did. or (JP-11045892-\$ or JP-10242567-\$ or JP-10242514-\$ or JP-10242569-\$).did. or (JP-2000332294-\$ or JP-2000004046-\$ or JP-2000188260-\$ or EP-395392-\$).did.) and (amorphous or crystalline or crystal) near12 (boron adj phosphide or bp or buffer or current-blocking or current adj blocking)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 14:09
-	13	((US-6392257-\$ or US-5326424-\$ or US-6069021-\$ or US-6316793-\$ or US-6150672-\$ or US-5612551-\$ or US-5929467-\$ or US-5042043-\$ or US-6194744-\$ or US-6064082-\$).did. or (US-20020038892-\$ or US-20020030246-\$ or US-20020000563-\$).did. or (JP-11045892-\$ or JP-10242567-\$ or JP-10242514-\$ or JP-10242569-\$).did. or (JP-2000332294-\$ or JP-2000004046-\$ or JP-2000188260-\$ or EP-395392-\$).did.) and (amorphous or crystalline or crystal) near12 (boron adj phosphide or bp or buffer or current-blocking or current adj blocking)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 15:47
-	212	oh.in. and won.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 15:48
-	18	oh.in. and won.in. and buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 15:48
-	4	oh.in. and won.in. and buffer and nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 16:37
-	2	("6069021").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 16:37
-	2	("5042043").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/15 17:45
-	344	mixed adj crystal near12 (single-crystal or single adj crystal or monocrystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/15 17:46
-	254	mixed adj crystal near6 (single-crystal or single adj crystal or monocrystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/15 17:47
-	145	mixed adj crystal near3 (single-crystal or single adj crystal or monocrystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/15 17:47

-	87	mixed adj crystal near3 (single-crystal or single adj crystal or monocrystal).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/15 17:47
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